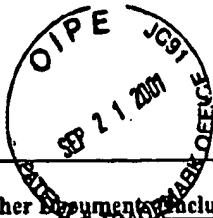


Form PTO 1449 (Rev. 2-32)		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. CAY-006		Serial No. 09/943,338		
Information Disclosure Statement by Applicant				Applicant: John M. Caywood				
(Use several sheets if necessary)				Filed: 8/28/2001 Group: (to be assigned) <b>2819</b>				
U.S. Patent Documents								
Init.		Document No.	Date	Name	Class	Subclass	Filing Date	
<b>A</b>	A	3,778,645	12/11/73	Mattauch et al.	307	318	1/31/72	
<b>B</b>	B	4,035,820	7/12/77	Matzen	357	23	12/29/75	
<b>C</b>	C	4,037,242	7/19/77	Gosney	357	23	12/29/75	
<b>D</b>	D	4,513,397	4/23/85	Ipri et al.	365	185	12/10/82	
<b>E</b>	E	4,626,887	12/2/86	Schmitt-Landsiedel et al.	357	43	8/2/84	
<b>F</b>	F	4,630,081	12/16/86	Calviello	357	6	12/19/84	
<b>G</b>	G	4,686,558	8/11/87	Adam	357	42	9/1/83	
<b>H</b>	H	4,752,912	6/21/88	Guterman	365	185	7/22/85	
<b>I</b>	I	4,907,197	3/6/90	Uchida	365	185	7/12/88	
<b>J</b>	J	4,907,198	3/6/90	Arima	365	185	11/2/88	
<b>K</b>	K	4,910,565	3/20/90	Masuoka	357	23.5	5/12/88	
<b>L</b>	L	4,924,437	5/8/90	Paterson et al.	365	185	12/9/87	
<b>M</b>	M	4,967,393	10/30/90	Yokoyama et al.	365	185	1/3/90	
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<b>S</b>	S	5,838,039	11/17/98	Sato et al.	257	321	7/8/96	
<b>T</b>	T	5,841,161	11/24/98	Lim et al.	257	315	3/3/97	
<b>U</b>	U	5,946,240	8/31/99	Hisamune	365	185.28	12/23/97	
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<b>W</b>	W	6,002,152	12/14/99	Guterman et al.	257	316	12/9/98	
Foreign Documents								
							Translation	
Init.		Document No.	Date	Country	Class	Subclass	Yes	No
<b>X</b>	X	2964412	10/18/99	Japan			X	



Other Documents (including Author, Title, Date, Pertinent Pages, etc.)	
Y	Dons, et al., "Direct Tunneling Diode Structure with a Multi-Layer Charge Injection Barrier", <i>29th IEEE Semiconductor Interface Specialists Conference</i> (1998)
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BB	Krolikowski, "Photoemission Studies of the Noble Metals. I. Copper", <i>Physical Review</i> , Vol. 185, No. 3, pp. 882-900 (1969)
CC	Krolikowski, "Photoemission Studies of the Noble Metals II. Gold", <i>Physical Review B</i> , Vol. 1, No. 2, pp. 478-487 (1970)
DD	Mead, "Operation of Tunnel-Emission Devices", <i>J. Appl. Phys.</i> , Vol. 32, No. 4 (1961)
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Examiner:	Date Considered 9/31/04
Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include a copy of this form with the next communication to applicant.	